

OSZ-2049023F-16V(AuSn)

SILICON ZENER DIODE

BIDIRECTIONAL ZENER DIODE (FLIP TYPE)

APPLICATION : Surge ESD Protector

● DIE SIZE

$0.47(\pm 0.02)\text{mm} \times 0.21(\pm 0.02)\text{mm}$
 $[18.50(\pm 0.79)\text{mil} \times 8.27(\pm 0.79)\text{mil}]$

● DIE THICKNESS

$120 \pm 20\mu\text{m}$ or $150 \pm 20\mu\text{m}$ or $210 \pm 20\mu\text{m}$
 $(4.72 \pm 0.79\text{mil}$ or $5.91 \pm 0.79\text{mil}$ or $8.27 \pm 0.79\text{mil})$

● METALLIZATION

TOP

AuSn

BOTTOM

None

● SOLDER THICKNESS

$3\mu\text{m}$

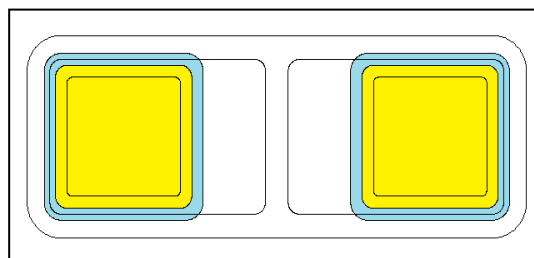
● BONDING PAD SIZE

ANODE(TOP)

$0.120\text{mm} \times 0.130\text{mm}$ ($4.72\text{mil} \times 5.12\text{mil}$)

CATHODE(TOP)

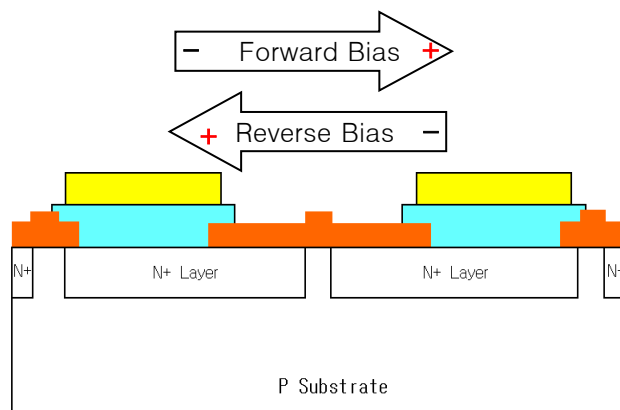
$0.120\text{mm} \times 0.130\text{mm}$ ($4.72\text{mil} \times 5.12\text{mil}$)



● ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Voltage	V_Z	$I_F=5\text{mA}$	13.0	16.0	19.0	V
Zener Voltage	V_Z	$I_Z=5\text{mA}$	13.0	16.0	19.0	V
Reverse Current	I_R	$V_R=10\text{V}$			0.1	μA
Forward Current	I_F	$V_F=10\text{V}$			0.1	μA

● THE DIRECTION OF BIAS IS USED TO ELECTRICAL CHARACTERISTICS TEST



● ABSOLUT MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Maximum Rating	Unit
Power Dissipation	P_d	50	mW
Junction Temperature	T_J	150	°C

● ORDER FORM

	THICKNESS(μm) ($\pm 20\mu\text{m}$)	THICKNESS(mil) ($\pm 0.79\text{mil}$)
OSZ-2049023F-16V12(AuSn)	120	4.72
OSZ-2049023F-16V15(AuSn)	150	5.91
OSZ-2049023F-16V21(AuSn)	210	8.27

BIDIRECTIONAL ZENER DIODE (FLIP TYPE)

PART NAME : ZENER DIODE

PART NUMBER : OSZ-2049023F-16V(AuSn)

